conduction type opposite to a channel formed in a surface layer of the channel forming region of said field effect transistor, in a lower portion of the channel forming region thereof to said body electrode and said back gate electrode or at least said back gate electrode so as to increase a threshold voltage of said field effect transistor.

13. (Amended) A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel forming region of said field effect transistor, comprising:

applying a potential lying in a direction to induce an electrical charge of conduction type opposite to a channel formed in a surface layer of the channel forming region of said field effect transistor, in a lower portion of the channel forming region thereof to said body electrode and said back gate electrode or at least said back gate electrode so as to stabilize a threshold voltage of said field effect transistor and increase a withstand voltage of the drain thereof.

Please add new claims 19-30 as follows:

19. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel region of said field effect transistor, comprising:

applying potentials to the body electrode and the back gate electrode so as to increase threshold voltage of the field effect transistor in an aging state for the semiconductor device.

20. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel region of said field effect transistor, comprising:

applying potentials to the body electrode and the back gate electrode so as to increase threshold voltage of the field effect transistor in a test state for measuring a leakage current.

21. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel region of said field effect transistor, comprising:

applying potentials to the body electrode and the back gate electrode which change with time such that the threshold voltage of the field effect transistor is increased or deceased in accordance with changes in time.

22. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect

transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel region of said field effect transistor, comprising:

applying potentials to the body electrode and the back gate electrode so as to increase threshold voltage of the field effect transistor, wherein the field effect transistor constitutes a predetermined circuit block, and activating another field effect transistor constituting another circuit block at high speed in a state of being brought to a low threshold voltage.

23. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer, a body electrode electrically connected to a channel forming region of said field effect transistor, and a back gate electrode provided below the insulating layer in an opposing relationship to the channel region of said field effect transistor, comprising steps of:

applying potentials to the body electrode and the back gate electrode so as to increase threshold voltage of the field effect transistor.

24. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according to claim 12, wherein said field effect transistor is a partial depletion-type field effect transistor.

25. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according

to claim 13, wherein said field effect transistor is a partial depletion-type field effect transistor.

26. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according to claim 19, wherein said field effect transistor is a partial depletion-type field effect transistor.

27. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according to claim 20, wherein said field effect transistor is a partial depletion-type field effect transistor.

28. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according to claim 21, wherein said field effect transistor is a partial depletion-type field effect transistor.

29. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according to claim 22, wherein said field effect transistor is a partial depletion-type field effect transistor.

30. A method of driving a semiconductor device having a field effect transistor formed in a semiconductor layer provided on an insulating layer according